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J. Smith

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

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TOMOHIRO YAMASHITA ET AL.

: GROUP ART UNIT: 2811

SERIAL NO.: 09/754,325

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FILED: JANUARY 5, 2001

: EXAMINER: NADAV, O

FOR: SEMICONDUCTOR DEVICE

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RECEIVED  
OCT 29 2002  
TECHNOLOGY CENTER 2800

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action dated July 25, 2002, please amend the above-identified patent application as follows:

IN THE SPECIFICATION

Please replace the paragraph on page 2, beginning on line 6, with the following:

a-  
An NMOSFET 91P is formed on the P well 11P, and a P-type semiconductor layer (hereinafter also referred to as "P-type layer") 21P for fixing the potential of the P well 11P is formed in the P well 11P. Similarly, an NMOSFET 92P different in characteristic from the aforementioned NMOSFET 91P is formed on the P well 12P, and a P-type layer 22P for fixing the potential of the P well 12P is formed in the P well 12P. While the P-type layers 21P and 22P are formed in the vicinity of the boundary between the P wells 11P and 12P in Fig. 22, the P-type layers 21P and 22P may alternatively be formed on other portions in the P wells 11P and 12P respectively. Element isolation films 51P and 51BP isolate the